TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7SH86F, TC7SH86FU

EXCLUSIVE OR GATE

The TC7SH86 is an advanced high speed CMOS EXCLUSIVE OR GATE fabricated with silicon gate CMOS technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

The internal circuit is includes on output buffer, which provide high noise immunity and stable output. An input protection circuit ensures that 0V to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V system and two supply system such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

FEATURES

- High Speed t_{pd} = 4.8ns (Typ.) at V_{CC} = 5V
- Low Power Dissipation \cdots $I_{CC} = 2\mu A$ (Max.) at $Ta = 25^{\circ}C$
- High Noise Immunity ······· V_{NIH} = V_{NIL} = 28% V_{CC} (Min.)
- Power Down Protection is provided on all inputs.
- Balanced Propagation Delays ······ t_{pLH}=t_{pHL}
- Wide Operation Voltage Range ··· V_{CC} (opr) = 2V~5.5V

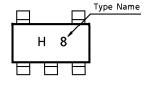
TC75H86F SSOP5-P-0.95 TC75H86FU SSOP5-P-0.65A

Weight SSOP5-P-0.95 : 0.016g (Typ.) SSOP5-P-0.65A : 0.006g (Typ.)

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	Vcc	-0.5~7.0	V
DC Input Voltage	VIN	-0.5~7.0	٧
DC Output Voltage	VOUT	-0.5~V _{CC} +0.5	٧
Input Diode Current	ΙΚ	- 20	mA
Output Diode Current	loк	± 20	mA
DC Output Current	IOUT	± 25	mΑ
DC V _{CC} /Ground Current	Icc	± 50	mΑ
Power Dissipation	PD	200	mW
Storage Temperature	T _{stg}	-65∼150	°C
Lead Temperature (10 s)	TL	260	°C

MARKING



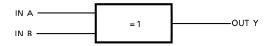
TRUTH TABLE

Α	В	Υ
L	L	L
L	Н	Н
I	L	Н
Н	Н	L

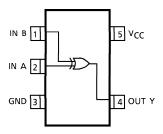
961001EBA2

[●] TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

LOGIC DIAGRAM



PIN ASSIGNMENT (TOP VIEW)



RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Supply Voltage	Vcc	2.0~5.5	V	
Input Voltage	VIN	0~5.5	V	
Output Voltage	VOUT	0~V _{CC}	V	
Operating Temperature	T _{opr}	- 40~85	°C	
Input Rise and Fall Time	dt/dv	$0 \sim 100 \text{ (V}_{CC} = 3.3 \pm 0.3 \text{V)}$	ns / V	
Input Rise and Fall Time	ut/uv	$0\sim20 \ (V_{CC} = 5 \pm 0.5 V)$] 113 / V	

DC ELECTRICAL CHARACTERISTICS

CHADACTERISTIC	CVAADOL	TEST CONDITION			Ta = 25°C			Ta = −40~85°C		UNIT	
CHARACTERISTIC	SYMBOL			VCC	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT	
High-Level				2.0	1.50	_		1.50			
Input Voltage	V _{IH}			3.0~ 5.5	V _{CC} ×0.7	_	_	V _{CC} ×0.7	1	V	
Low-Level				2.0		_	0.50	_	0.50		
Input Voltage	V _{IL}			3.0~ 5.5	1	_	V _C C ×0.3	_	V _C C ×0.3	V	
	Voн		I _{OH} = -50μA	2.0	1.9	2.0	_	1.9	_	V	
Liab Laval		V _{IN} = V _{IH} or V _{IL}		3.0	2.9	3.0	_	2.9	_		
High-Level Output Voltage				4.5	4.4	4.5	_	4.4	_		
			$I_{OH} = -4mA$	3.0	2.58	_	_	2.48	_		
			$I_{OH} = -8mA$	4.5	3.94	_	_	3.80	_		
	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 50μA	2.0	_	0.0	0.1		0.1		
Low-Level				3.0		0.0	0.1	_	0.1		
Output Voltage				4.5	_	0.0	0.1		0.1		
Output Voltage			$I_{OL} = 4mA$	3.0	_		0.36		0.44		
			$I_{OL} = 8mA$	4.5		1	0.36	—	0.44]	
Input Leakage Current	lIN	V _{IN} = 5.5V or GND		0~ 5.5			± 0.1		± 1.0	μΑ	
Quiescent Supply Current	lcc	V _{IN} = V _{CC} or GND		5.5			2.0	_	20.0	μΑ	

961001EBA2'

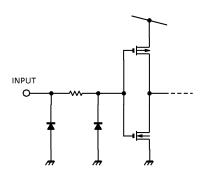
The products described in this document are subject to foreign exchange and foreign trade control laws.
 The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
 The information contained herein is subject to change without notice.

AC	ELECTRICAL	CHARACTERISTICS	(Input t	$r = t_f = 3ns$
----	-------------------	------------------------	----------	-----------------

CHARACTERISTIC	SYMBOL	TEST C	TEST CONDITION		Ta = 25°C			Ta = -40~85°C		UNIT
			V _{CC} (V)	C _L (pF)	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
Propagation Delay Time	t _{pLH}		22+02	15	1	7.0	11.0	1.0	13.0	ns
			3.3 ± 0.3	50	_	9.5	14.5	1.0	16.5	
			5.0 ± 0.5	15	_	4.8	6.8	1.0	8.0	
				50	_	6.3	8.8	1.0	10.0	
Input Capacitance	CIN				_	4	10	_	10	рF
Power Dissipation Capacitance	C _{PD}	(Note 1)		_	18	_	_	_	pF	

(Note 1): CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation : $I_{CC}(opr) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

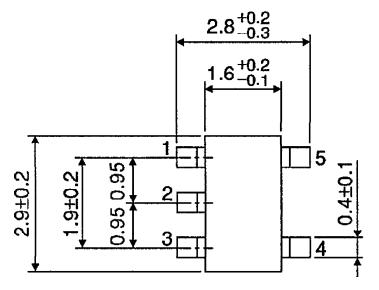
INPUT EQUIVALENT CIRCUIT

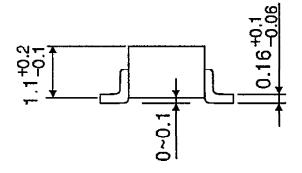


OUTLINE DRAWING

SSOP5-P-0.95

Unit: mm



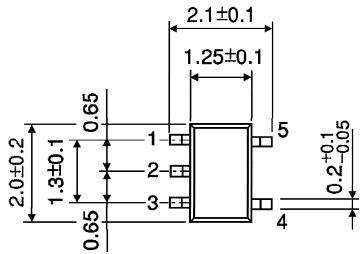


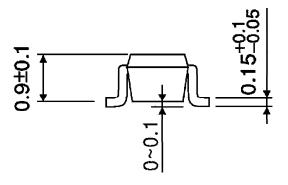
Weight: 0.016g (Typ.)

Unit: mm

OUTLINE DRAWING

SSOP5-P-0.65A





Weight: 0.006g (Typ.)